

In the Claims:

Claim 9 has been amended as follows:

9. (Amended) A method to pattern a polysilicon layer in the manufacture of an integrated circuit device comprising:

providing a polysilicon layer overlying a semiconductor substrate;

5 providing a hard mask layer overlying said polysilicon layer;

providing a silicon dioxide layer overlying said hard mask layer;

providing a resist layer overlying said hard mask layer;

10 patterning said resist layer to form a resist mask that exposes a part of said hard mask layer;

patterning said polysilicon layer wherein said patterning is performed sequentially in a dry plasma etch chamber and wherein said patterning comprises:

15 etching said resist mask to trim said resist mask;

thereafter etching said hard mask layer exposed by said resist mask to form a hard mask that exposes a part of said polysilicon layer;

thereafter stripping away said resist mask;

20 thereafter cleaning away polymer residue from said resist

mask wherein said cleaning away comprises a chemistry  
containing  $\text{CF}_4$  gas; and

thereafter etching said polysilicon layer exposed by  
said hard mask; and

stripping away said hard mask to complete the patterning  
of said polysilicon layer in the manufacture of the integrated  
circuit device.

Please cancel Claim 16.

Claim 17 has been amended as follows:

16 17. (Amended) A method to pattern a polysilicon layer in the  
manufacture of an integrated circuit device comprising:

providing a gate oxide layer overlying a semiconductor  
substrate;

5 providing a polysilicon layer overlying said gate oxide  
layer;

providing a silicon oxynitride layer overlying said  
polysilicon layer;

providing a silicon dioxide layer overlying said silicon  
10 oxynitride layer;

providing a resist layer overlying said silicon dioxide layer;

patterning said resist layer to form a resist mask that exposes a part of said silicon dioxide layer;

15       patterning said polysilicon layer wherein said patterning is performed sequentially in a dry plasma etch chamber and wherein said patterning comprises:

etching said resist mask to trim said resist mask;

20       thereafter etching said silicon dioxide layer and said silicon oxynitride layer exposed by said resist mask to form a hard mask that exposes a part of said polysilicon layer;

thereafter stripping away said resist mask;

25       thereafter cleaning away polymer residue from said resist mask wherein said cleaning away comprises a chemistry containing  $CF_4$  gas; and

thereafter etching said polysilicon layer exposed by said hard mask wherein said etching comprises a main etch step followed by an overetch step; and

30       stripping away said hard mask to complete the patterning of said polysilicon layer in the manufacture of the integrated circuit device.